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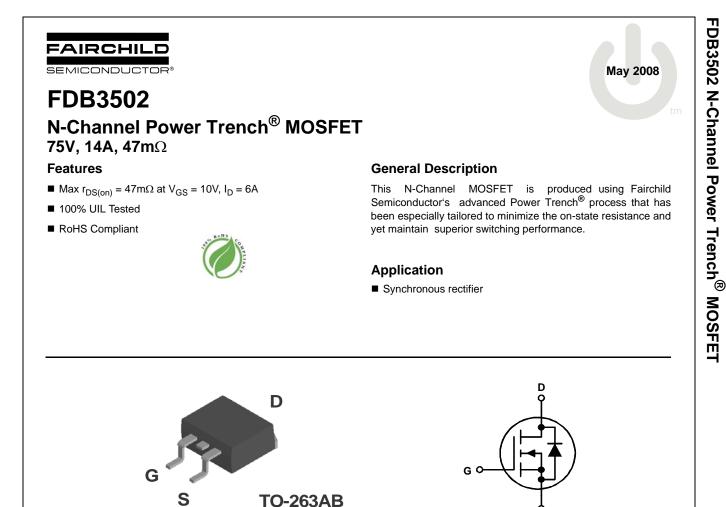


# **ON Semiconductor**®

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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="mailto:www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to <a href="mailto:Fairchild\_questions@onsemi.com">Fairchild\_questions@onsemi.com</a>.

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## MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

**FDB Series** 

Symbol	Parameter			Ratings	Units	
V <sub>DS</sub>	Drain to Source Voltage			75	V	
V <sub>GS</sub>	Gate to Source Voltage			±20	V	
ID	Drain Current -Continuous (Package limited)	T <sub>C</sub> = 25°C		14		
	-Continuous (Silicon limited)	T <sub>C</sub> = 25°C		22		
	-Continuous	T <sub>A</sub> = 25°C	(Note 1a)	6	Α	
	-Pulsed			40		
E <sub>AS</sub>	Single Pulse Avalanche Energy		(Note 3)	54	mJ	
D	Power Dissipation	T <sub>C</sub> = 25°C		41		
PD	Power Dissipation $T_A = 25^{\circ}C$ (Note 1a)		(Note 1a)	3.1	W	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature R	ange		-55 to +150	°C	

### **Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance, Junction to Case		3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	40	C/vv

#### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB3502	FDB3502	TO-263AB	330 mm	24 mm	800 units

FDB3502
N-Channe
Power
Trench®
MOSFET

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_{D} = 250 \mu A, V_{GS} = 0 V$	75			V
ΔBV <sub>DSS</sub> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu A$ , referenced to 25°C		70		mV/°C
IDSS	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 60V,$			1	μA
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			±100	nA
On Chara	cteristics					
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	2.5	3.8	4.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$ , referenced to 25°C		-10		mV/°C
	Static Drain to Source On Resistance	$V_{GS} = 10V, I_D = 6A$		37	47	
rDS(on)		$V_{GS} = 10V, I_D = 6A, T_J = 125^{\circ}C$		63	80	mΩ
9 <sub>FS</sub>	Forward Transconductance	$V_{DD} = 10V, I_D = 6A$		13		S
	Characteristics					-
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V,		615	815	pF
C <sub>oss</sub>	Output Capacitance	f = 1MHz		75	105	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	6 ANU -		35	40	pF
R <sub>g</sub>	Gate Resistance	f = 1MHz		1.5		Ω
Switching	g Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time			9	17	ns
t <sub>r</sub>	Rise Time	$V_{DD} = 40V, I_D = 6A,$		3	10	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS}$ = 10V, $R_{GEN}$ = 6 $\Omega$		13	22	ns
t <sub>f</sub>	Fall Time			3	10	ns
Qg	Total Gate Charge at 10V	1/ 401/		11	15	nC
Q <sub>gs</sub>	Gate to Source Charge	$V_{DD} = 40V$ $I_D = 6A$		4		nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge	-D = 0, (		3		nC
Drain-Sou	urce Diode Characteristics					
	Source to Drain Diode, Ferward Valters	$V_{GS} = 0V, I_S = 2.6A$ (Note 2)		0.78	1.2	V
V <sub>SD</sub>	Source to Drain Diode Forward Voltage	$V_{GS} = 0V, I_S = 6A$ (Note 2)		0.83	1.3	v

Notes:

t<sub>rr</sub>

 $Q_{rr}$ 

1:  $R_{0JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{0JC}$  is guaranteed by design while  $R_{0JA}$  is determined by the user's board design.

 $I_F = 6A$ , di/dt = 100A/µs

a. 40°C/W when mounted on a 1 in  $^2\,\text{pad}$  of 2 oz copper b. 62.5°C/W when mounted on a minimum pad.

Reverse Recovery Time

Reverse Recovery Charge

2: Pulse Test: Pulse Width < 300µs, Duty cycle < 2.0%.

3: Starting  $T_J = 25^{\circ}C$ , L = 3mH,  $I_{AS} = 6A$ ,  $V_{DD} = 75V$ ,  $V_{GS} = 10V$ .

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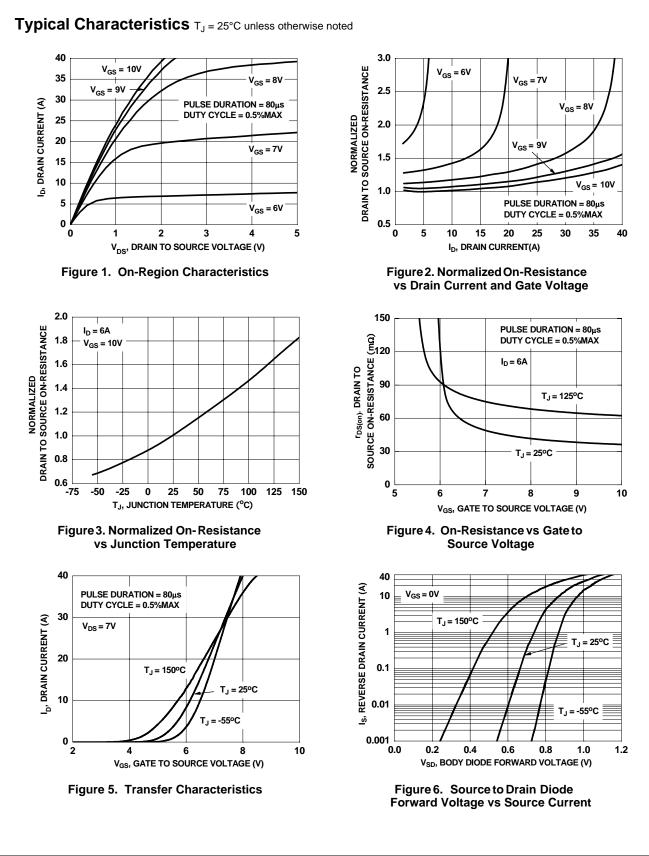
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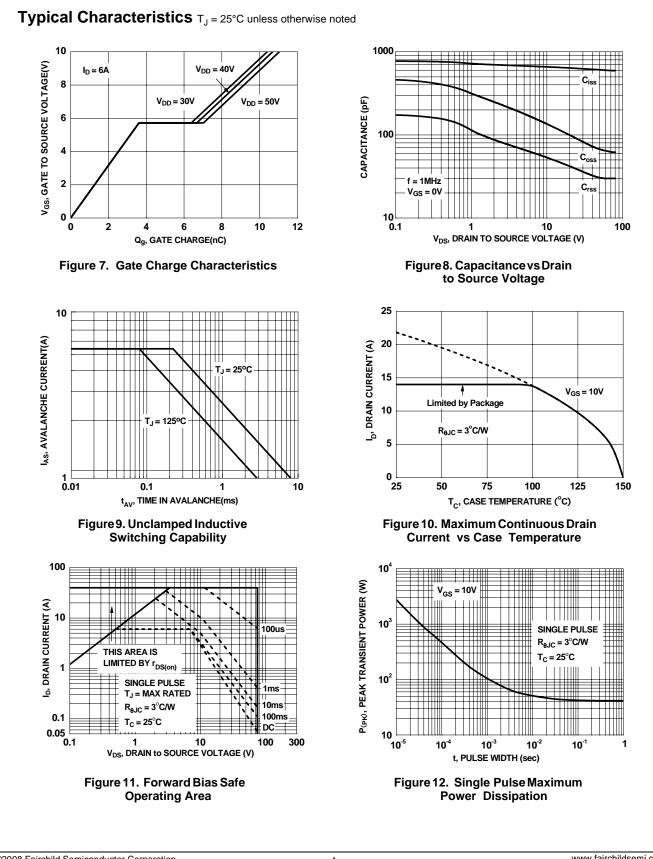
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nC



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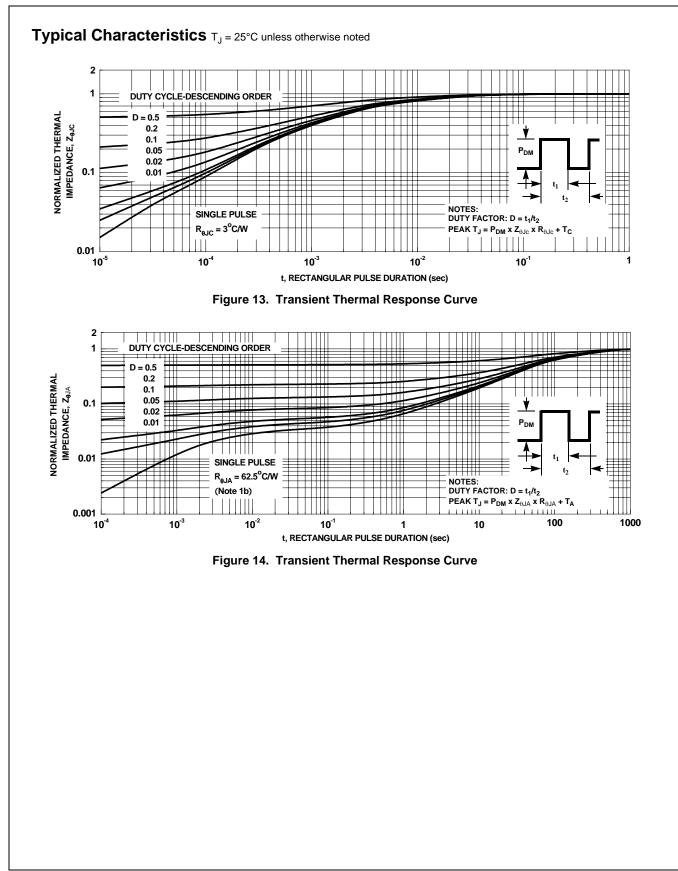


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FDB3502 N-Channel Power Trench<sup>®</sup> MOSFET



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